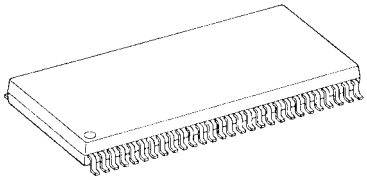
TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCXR162543FT

Low-Voltage 16-Bit Registered Transceiver with 3.6-V Tolerant Inputs and Outputs



TSSOP56-P-0061-0.50

Weight: 0.25 g (typ.)

The TC74VCXR162543FT is a high-performance CMOS 16-bit registered transceiver. Designed for use in 1.8-V, 2.5-Vor 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

The TC74VCXR162543FT can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{\text{LEAB}}$ or $\overline{\text{LEBA}}$) and output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{\text{CEAB}}$) input must be low in order to enter data from A or to output data from B. If $\overline{\text{CEAB}}$ is low and $\overline{\text{LEAB}}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{\text{LEAB}}$ puts the Alatches in the storage mode. With $\overline{\text{CEAB}}$ and $\overline{\text{OEAB}}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches.

Data flow from B to A is similar but requires using the $\overline{\text{CEBA}}$, $\overline{\text{LEBA}}$, and $\overline{\text{OEBA}}$ inputs.

When the $\overline{\text{OE}}$ input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The 26-Ω series resistor helps reducing output overshoot and undershoot without external resistor.

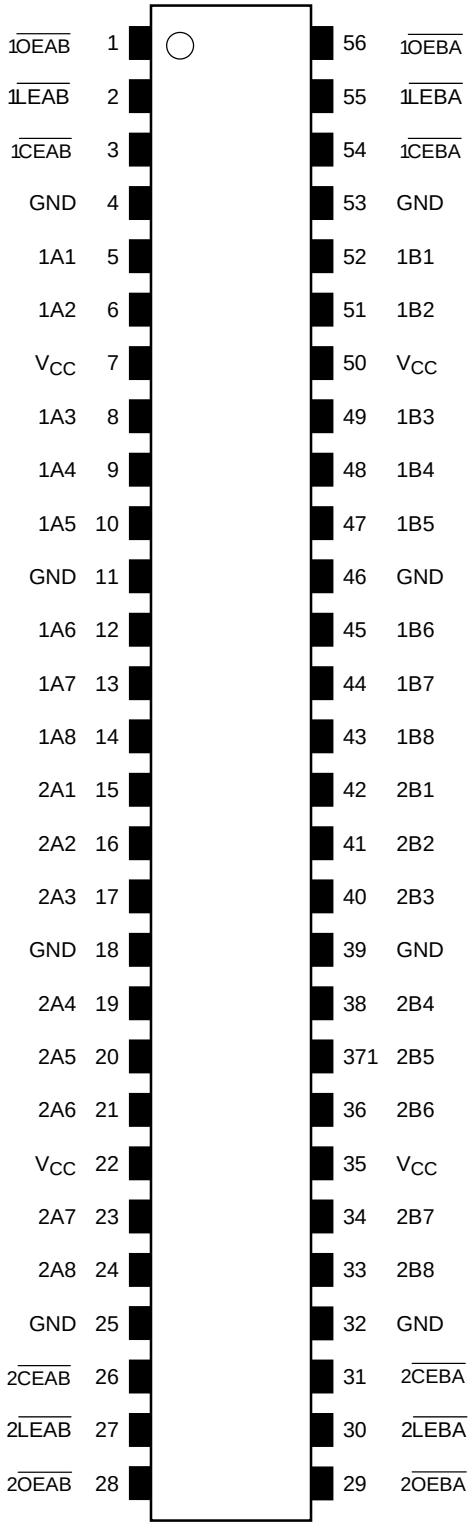
All inputs are equipped with protection circuits against static discharge.

Features

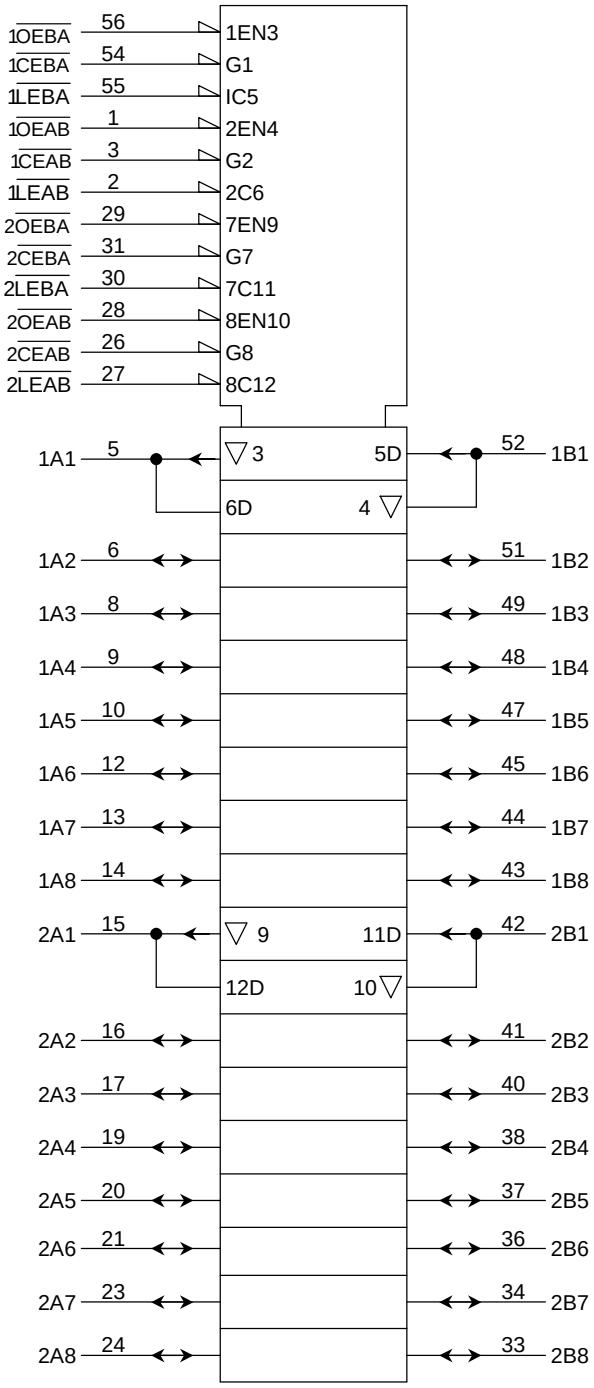
- 26-Ω series resistors on outputs
- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- High-speed operation: t_{pd} = 4.4 ns (max) (V_{CC} = 3.0 to 3.6 V)
  : t_{pd} = 5.4 ns (max) (V_{CC} = 2.3 to 2.7 V)
  : t_{pd} = 9.8 ns (max) (V_{CC} = 1.8 V)
- Output current: I_{OH}/I_{OL} = ±12 mA (min) (V_{CC} = 3.0 V)
  : I_{OH}/I_{OL} = ±8 mA (min) (V_{CC} = 2.3 V)
  : I_{OH}/I_{OL} = ±4 mA (min) (V_{CC} = 1.8 V)
- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V
  : Human body model > ±2000 V
- Package: TSSOP (thin shrink small outline package)
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Note 1: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.
All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

Pin Assignment (top view)



IEC Logic Symbol



Truth Table (A bus → B bus each 8-bit latch)

Inputs				Outputs B
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B0 (Note 2)
L	L	L	L	L
L	L	L	H	H

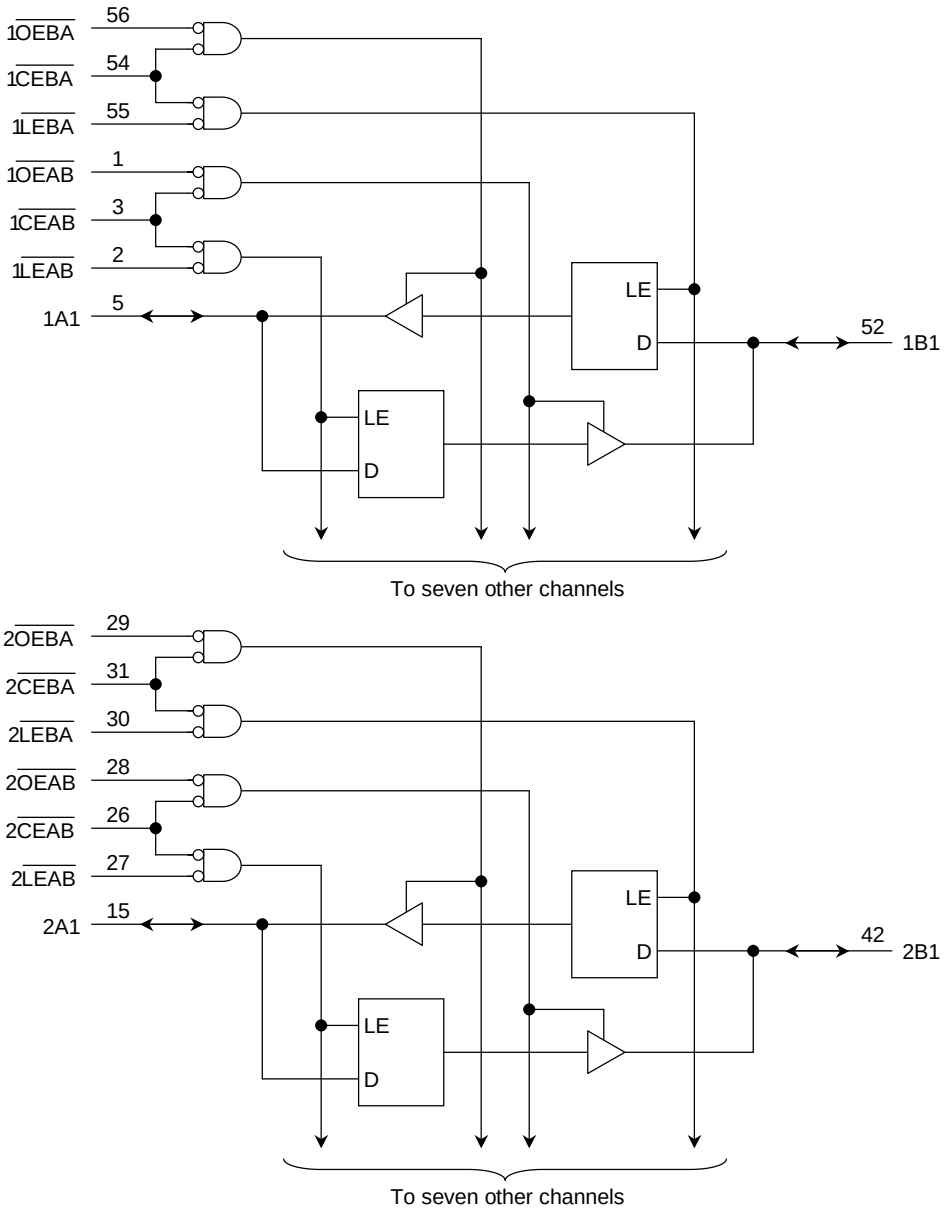
Note 2: Output level before the indicated steady-state input conditions were established.

Truth Table (B bus → A bus each 8-bit latch)

Inputs				Outputs A
$\overline{CEBA}$	$\overline{LEBA}$	$\overline{OEBA}$	B	
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	A0 (Note 2)
L	L	L	L	L
L	L	L	H	H

Note 2: Output level before the indicated steady-state input conditions were established.

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	−0.5 to 4.6	V
DC input voltage ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{LEAB}$, LEBA , CEAB , $\overline{CEBA}$)	V_{IN}	−0.5 to 4.6	V
DC bus I/O voltage	$V_{I/O}$	−0.5 to 4.6 (Note 3)	V
		−0.5 to V_{CC} + 0.5 (Note 4)	
Input diode current	I_{IK}	−50	mA
Output diode current	I_{OK}	±50 (Note 5)	mA
DC output current	I_{OUT}	±50	mA
Power dissipation	P_D	400	mW
DC V_{CC}/ground current per supply pin	I_{CC}/I_{GND}	±100	mA
Storage temperature	T_{stg}	−65 to 150	°C

Note 3: OFF state

Note 4: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 5: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 6)	
Input voltage ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{LEAB}$, LEBA , CEAB , $\overline{CEBA}$)	V_{IN}	−0.3 to 3.6	V
Bus I/O voltage	$V_{I/O}$	0 to 3.6 (Note 7)	V
		0 to V_{CC} (Note 8)	
Output current	I_{OH}/I_{OL}	±12 (Note 9)	mA
		±8 (Note 10)	
		±4 (Note 11)	
Operating temperature	T_{opr}	−40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 12)	ns/V

Note 6: Data retention only

Note 7: OFF state

Note 8: High or low state

Note 9: V_{CC} = 3.0 to 3.6 V

Note 10: V_{CC} = 2.3 to 2.7 V

Note 11: V_{CC} = 1.8 V

Note 12: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC Characteristics (Ta = –40 to 85°C, 2.7 V < V_{CC} ≦ 3.6 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	H-level	V_{IH}	—		2.7 to 3.6	2.0	—	V
	L-level	V_{IL}	—		2.7 to 3.6	—	0.8	
Output voltage	H-level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = –100 μA	2.7 to 3.6	V_{CC} – 0.2	—	V
				I_{OH} = –6 mA	2.7	2.2	—	
				I_{OH} = –8 mA	3.0	2.4	—	
				I_{OH} = –12 mA	3.0	2.2	—	
	L-level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.7 to 3.6	—	0.2	
				I_{OL} = 6 mA	2.7	—	0.4	
				I_{OL} = 8 mA	3.0	—	0.5	
				I_{OL} = 12 mA	3.0	—	0.8	
Input leakage current		I_{IN}	V_{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA
3-state output OFF state current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA
Power-off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		2.7 to 3.6	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.7 to 3.6	—	±20.0	
Increase in I_{CC} per input		ΔI_{CC}	V_{IH} = V_{CC} – 0.6 V		2.7 to 3.6	—	750	

DC Characteristics (Ta = –40 to 85°C, 2.3 V ≦ V_{CC} ≦ 2.7 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	H-level	V_{IH}	—		2.3 to 2.7	1.6	—	V
	L-level	V_{IL}	—		2.3 to 2.7	—	0.7	
Output voltage	H-level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = –100 μA	2.3 to 2.7	V_{CC} – 0.2	—	V
				I_{OH} = –4 mA	2.3	2.0	—	
				I_{OH} = –6 mA	2.3	1.8	—	
				I_{OH} = –8 mA	2.3	1.7	—	
	L-level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.3 to 2.7	—	0.2	
				I_{OL} = 6 mA	2.3	—	0.4	
				I_{OL} = 8 mA	2.3	—	0.6	
Input leakage current		I_{IN}	V_{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA
3-state output OFF state current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA
Power-off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		2.3 to 2.7	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.3 to 2.7	—	±20.0	

DC Characteristics (Ta = –40 to 85°C, 1.8 V ≦ V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	H-level	V_{IH}	—		1.8 to 2.3	0.7 × V_{CC}	—	V
	L-level	V_{IL}	—		1.8 to 2.3	—	0.2 × V_{CC}	
Output voltage	H-level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = –100 μA	1.8	V_{CC} – 0.2	—	V
				I_{OH} = –4 mA	1.8	1.4	—	
	L-level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.8	—	0.2	
				I_{OL} = 4 mA	1.8	—	0.3	
Input leakage current		I_{IN}	V_{IN} = 0 to 3.6 V		1.8	—	±5.0	μA
3-state output OFF state current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0 to 3.6 V		1.8	—	±10.0	μA
Power-off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		1.8	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		1.8	—	±20.0	

AC Characteristics (Ta = –40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500\ \Omega$)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Min	Max	Unit
Propagation delay time (An, Bn-Bn, An)	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.4	
			3.3 ± 0.3	0.6	4.4	
Propagation delay time ($\overline{LEAB}$, $\overline{LEBA}$ -Bn, An)	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.4	
			3.3 ± 0.3	0.6	4.8	
3-state output enable time ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	t_{pZL} t_{pZH}	Figure 1, Figure 4	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.9	
			3.3 ± 0.3	0.6	4.3	
3-state output disable time ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	t_{pLZ} t_{pHZ}	Figure 1, Figure 4	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	4.3	
Minimum pulse width ($\overline{LEAB}$, $\overline{LEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	$t_{W\ (L)}$	Figure 1, Figure 2, Figure 3	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum setup time (An, Bn-$\overline{LE}$, $\overline{CE}$)	t_s	Figure 1, Figure 2, Figure 3	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time (An, Bn-$\overline{LE}$, $\overline{CE}$)	t_h	Figure 1, Figure 2, Figure 3	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	t_{osLH} t_{osHL}	(Note 13)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 13: Parameter guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic Switching Characteristics
(Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500\ \Omega$)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V_{OL}	V_{OLP}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note 14)	1.8	0.15	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note 14)	2.5	0.25	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note 14)	3.3	0.35	
Quiet output minimum dynamic V_{OL}	V_{OLV}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note 14)	1.8	−0.15	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note 14)	2.5	−0.25	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note 14)	3.3	−0.35	
Quiet output minimum dynamic V_{OH}	V_{OHV}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note 14)	1.8	1.55	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note 14)	2.5	2.05	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note 14)	3.3	2.65	

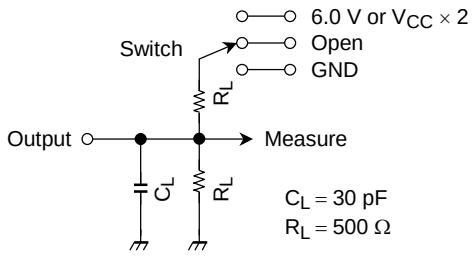
Note 14: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Typ.	Unit
Input capacitance	C_{IN}	($\overline{OEAB}$, $\overline{OEBA}$, $\overline{LEAB}$, $\overline{LEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	$C_{I/O}$	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C_{PD}	f_{IN} = 10 MHz (Note 15)	1.8, 2.5, 3.3	20	pF

Note 15: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:
$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16$ (per bit)

AC Test Circuit



Parameter	Switch	
t_{pLH}, t_{pHL}	Open	
t_{pLZ}, t_{pZL}	6.0 V $V_{CC} \times 2$	@V_{CC} = 3.3 ± 0.3 V @V_{CC} = 2.5 ± 0.2 V @V_{CC} = 1.8 V
t_{pHZ}, t_{pZH}	GND	

Figure 1

AC Waveform

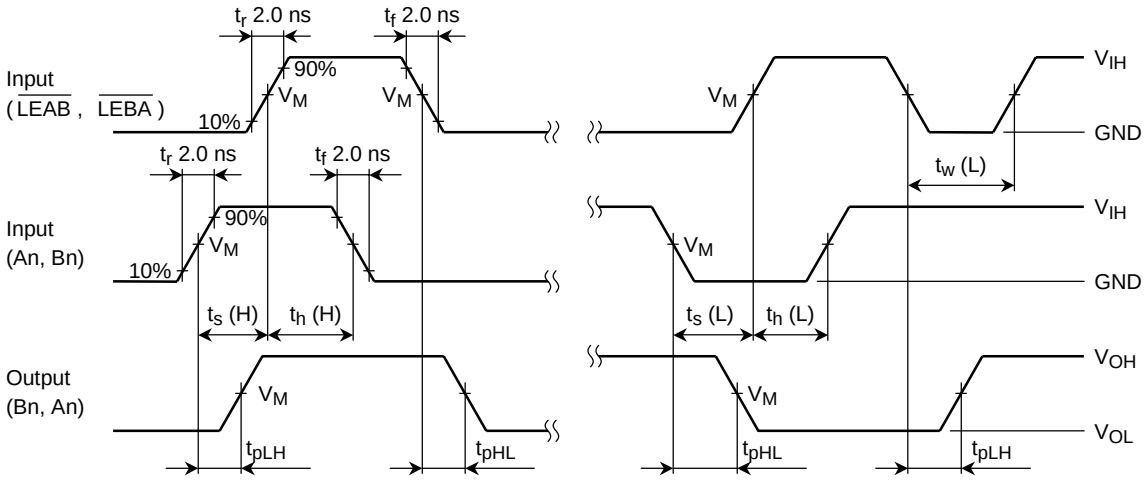


Figure 2 t_{pLH}, t_{pHL}, t_w, t_s, t_h

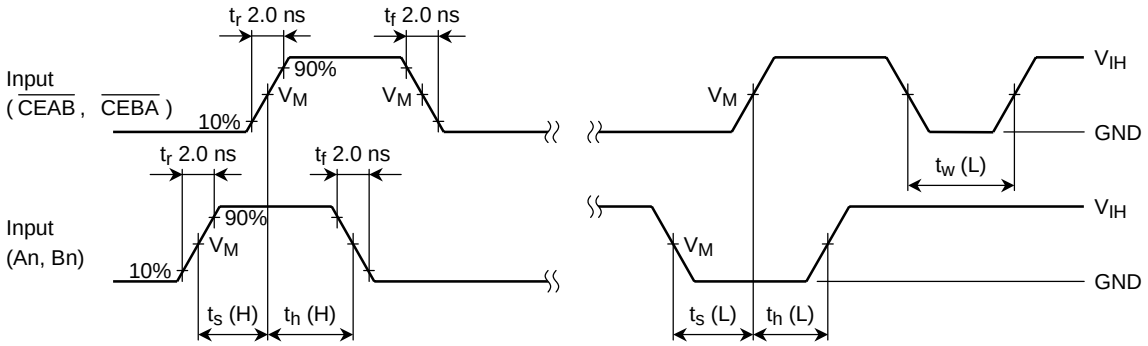


Figure 3 t_w, t_s, t_h

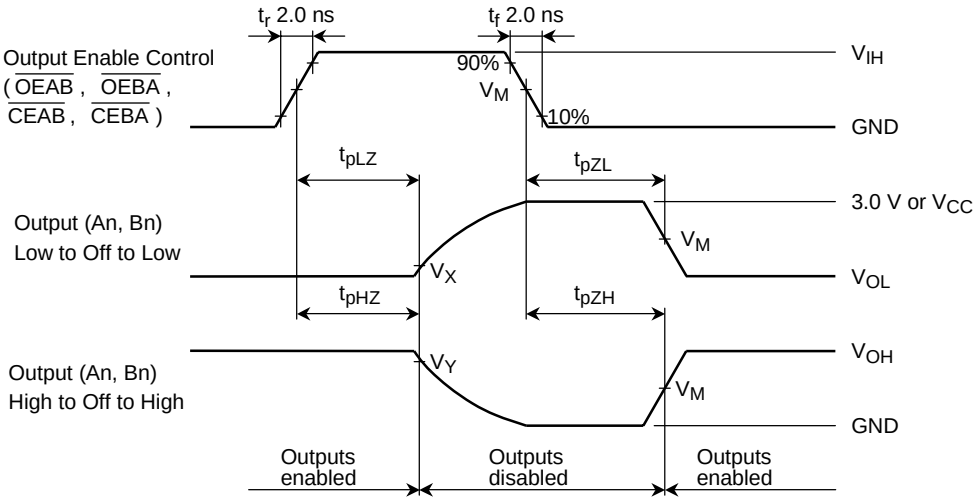
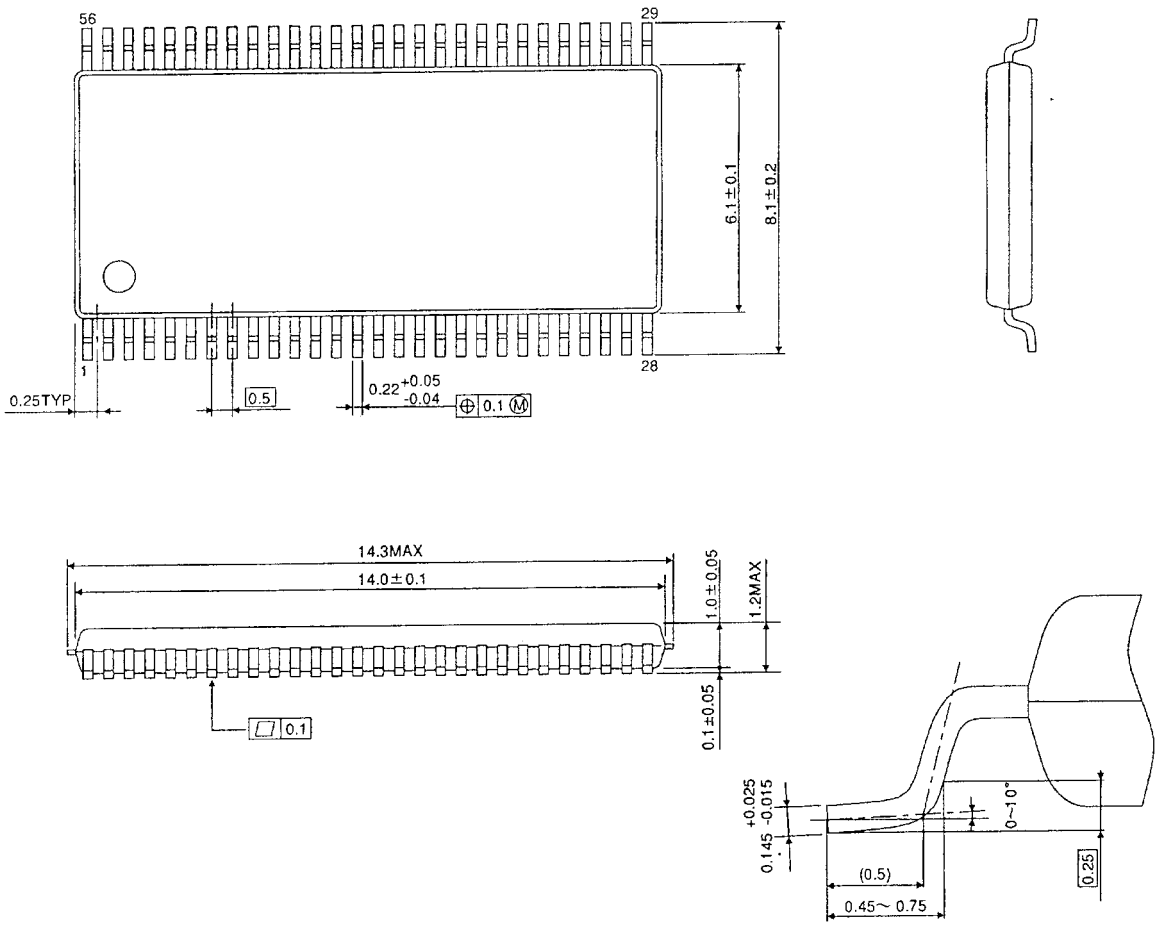


Figure 4 t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}

Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	V_{OL} + 0.3 V	V_{OL} + 0.15 V	V_{OL} + 0.15 V
V_Y	V_{OH} − 0.3 V	V_{OH} − 0.15 V	V_{OH} − 0.15 V

Package Dimensions

TSSOP56-P-0061-0.50 Unit : mm



Weight: 0.25 g (typ.)

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